

# N-channel TrenchMOS standard level FET

Rev. 2 — 2 February 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

### **1.3 Applications**

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

	Guick reference ua	ta				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	63	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	200	W
Static cha	racteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	20	mΩ
Avalanche	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 60 \text{ A};  \text{V}_{\text{sup}} \leq 100 \text{ V}; \\ R_{\text{GS}} &= 50  \Omega;  \text{V}_{\text{GS}} = 10  \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	400	mJ

### Suitable for standard level gate drive sources

Suitable for thermally demanding environments due to 175 °C rating

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Motors, lamps and solenoids

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# 2. Pinning information

Table 2.	Pinning information			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

# 3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7620-100A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

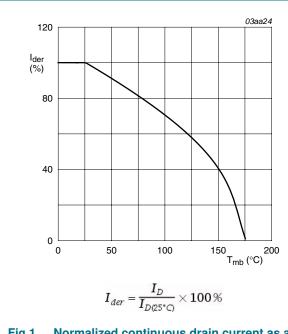
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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	63	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	44	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>	-	253	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	200	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	63	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	253	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 60 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	400	mJ





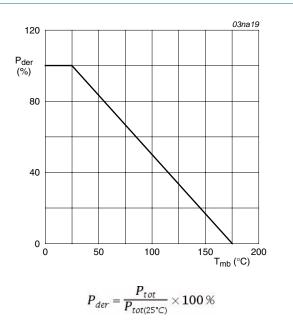
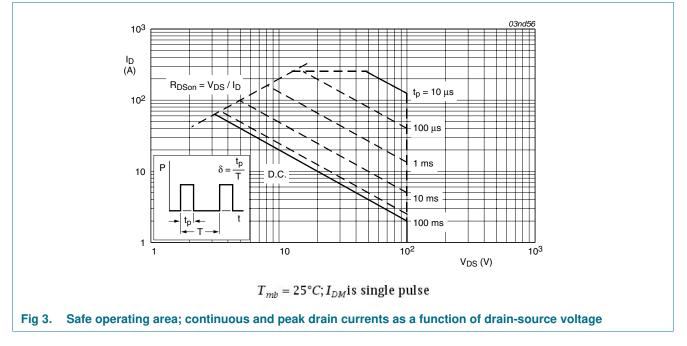


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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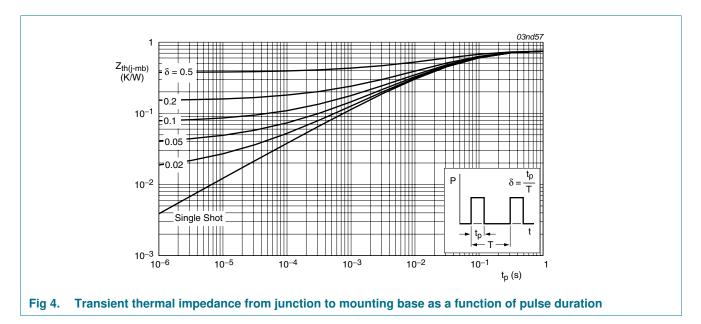
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### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.75	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint	-	50	-	K/W



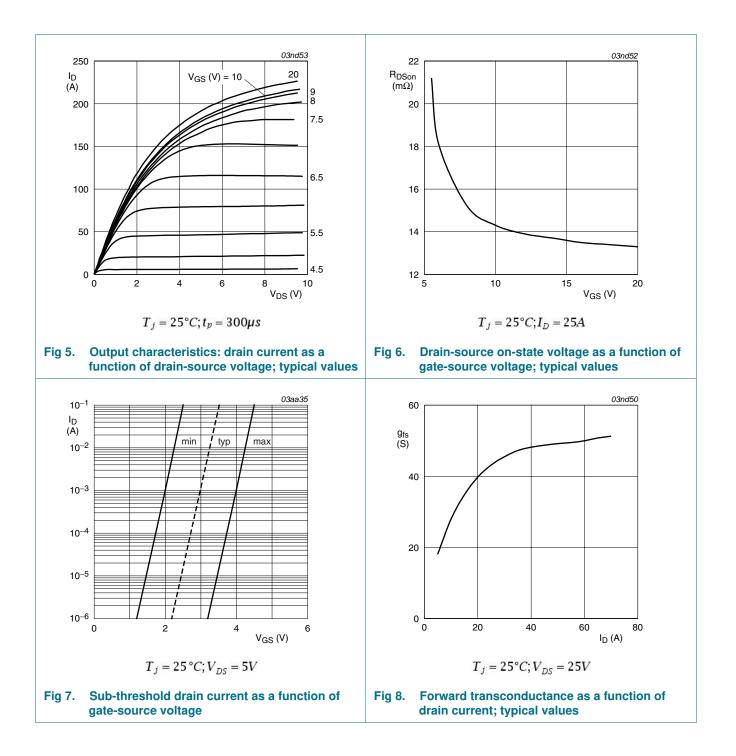
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### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
	breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	89	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; see <u>Figure 11</u>	-	-	4.4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	10	μA
		$V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	17	20	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	3430	4373	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	440	525	pF
C <sub>rss</sub>	reverse transfer capacitance		-	260	352	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_{L}$ = 1.2 $\Omega$ ; $V_{GS}$ = 10 V;	-	21	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C	-	87	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	108	-	ns
t <sub>f</sub>	fall time		-	56	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; T <sub>j</sub> = 25 °C	-	4.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; T <sub>j</sub> = 25 °C	-	7.5	-	nH
Source-d	rain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;	-	76	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C	-	282	-	nC

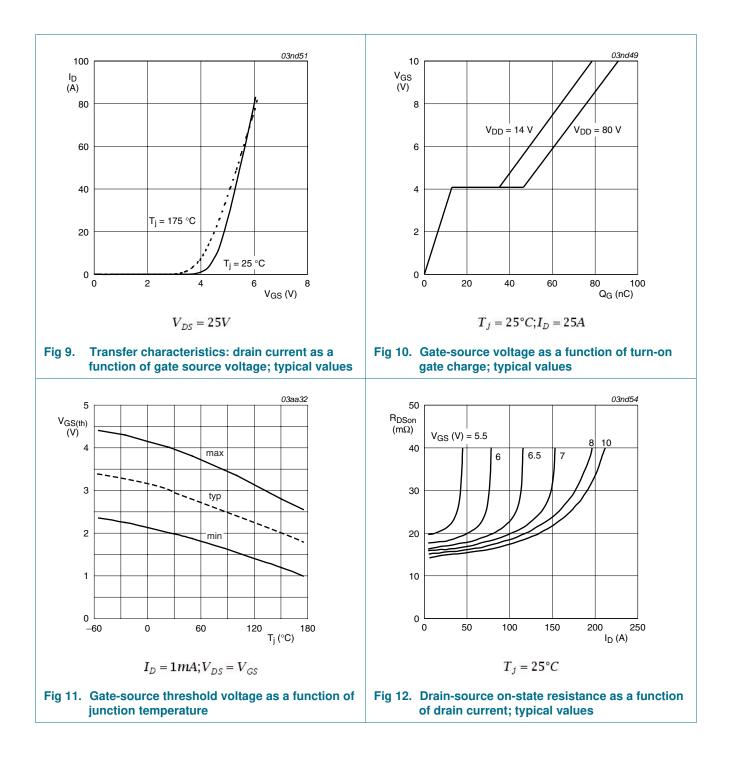
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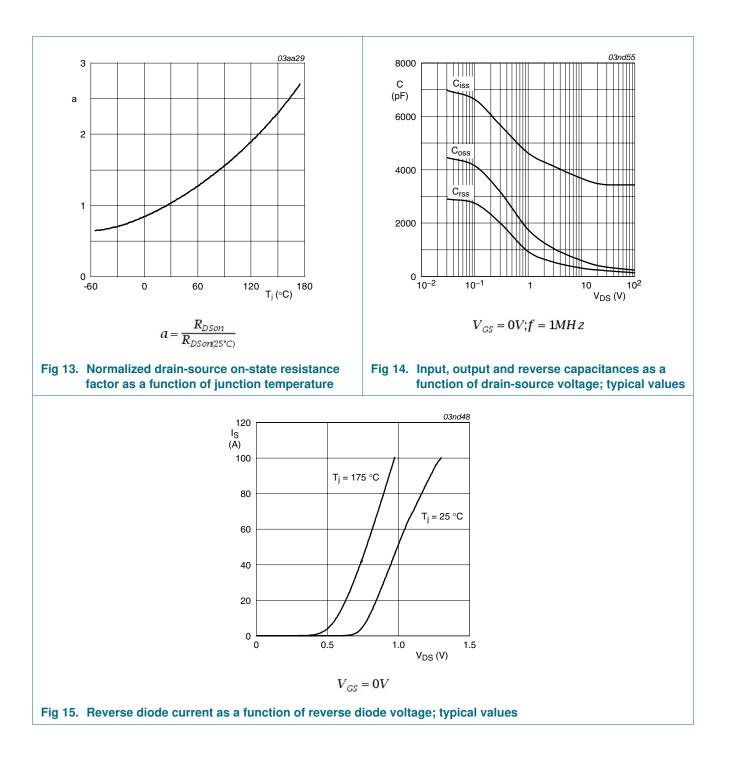
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# BUK7620-100A

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### 7. Package outline

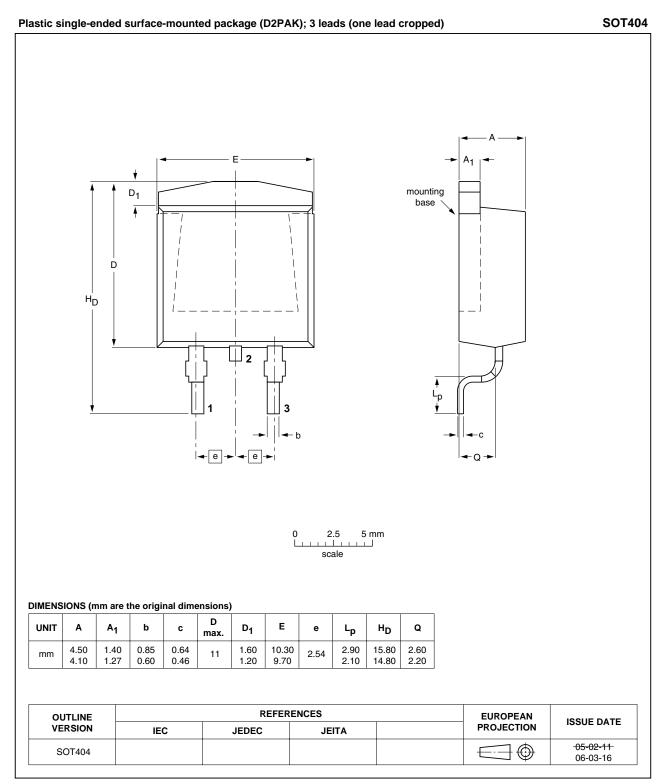


Fig 16. Package outline SOT404 (D2PAK)

BUK7620-100A Product data sheet

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# 8. Revision history

Table 7.	<b>Revision history</b>				
Documen	t ID	Release date	Data sheet status	Change notice	Supersedes
BUK7620-	100A v.2	20110202	Product data sheet	-	BUK7520_7620_100A-01
Modifications:		guidelines c	of NXP Semiconductors.	5	omply with the new identity
		0	have been adapted to the	1 3	
		<ul> <li>Type number</li> </ul>	er BUK7620-100A separa	ated from data she	et BUK7520_7620_100A-01.
BUK7520	_7620_100A-01	20010205	Product specification	-	-

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### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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